Alan C Farrell

List of Publications by Year
in descending order

21 papers	599 citations	623734 14 h-index	794594 19 g-index
22 all docs	22 docs citations	22 times ranked	875 citing authors

#	Article	IF	Citations
1	Monolithic InGaAs Nanowire Array Lasers on Silicon-on-Insulator Operating at Room Temperature. Nano Letters, 2017, 17, 3465-3470.	9.1	91
2	Monolithically Integrated InGaAs Nanowires on 3D Structured Silicon-on-Insulator as a New Platform for Full Optical Links. Nano Letters, 2016, 16, 1833-1839.	9.1	69
3	Telecom-Wavelength Bottom-up Nanobeam Lasers on Silicon-on-Insulator. Nano Letters, 2017, 17, 5244-5250.	9.1	54
4	Room-Temperature Midwavelength Infrared InAsSb Nanowire Photodetector Arrays with Al₂O₃ Passivation. Nano Letters, 2019, 19, 2793-2802.	9.1	52
5	High-Quality InAsSb Nanowires Grown by Catalyst-Free Selective-Area Metalâ€“Organic Chemical Vapor Deposition. Nano Letters, 2015, 15, 6614-6619.	9.1	44
6	InGaAsâ€“GaAs Nanowire Avalanche Photodiodes Toward Single-Photon Detection in Free-Running Mode. Nano Letters, 2019, 19, 582-590.	9.1	40
7	Thin 3D Multiplication Regions in Plasmonically Enhanced Nanopillar Avalanche Detectors. Nano Letters, 2012, 12, 6448-6452.	9.1	39
8	High Quantum Efficiency Nanopillar Photodiodes Overcoming the Diffraction Limit of Light. Nano Letters, 2016, 16, 199-204.	9.1	38
9	Uncooled Photodetector at Short-Wavelength Infrared Using InAs Nanowire Photoabsorbers on InP with pâ€“n Heterojunctions. Nano Letters, 2018, 18, 7901-7908.	9.1	35
10	Diode Characteristics Approaching Bulk Limits in GaAs Nanowire Array Photodetectors. Nano Letters, 2017, 17, 2420-2425.	9.1	25
11	Plasmonic field confinement for separate absorption-multiplication in InGaAs nanopillar avalanche photodiodes. Scientific Reports, 2015, 5, 17580.	3.3	21
12	Seeding layer assisted selective-area growth of As-rich InAsP nanowires on InP substrates. Nanoscale, 2017, 9, 8220-8228.	5.6	16
13	Catalyst-free selective-area epitaxy of GaAs nanowires by metal-organic chemical vapor deposition using triethylgallium. Nanotechnology, 2018, 29, 085601.	2.6	16
14	Nanopillar array band-edge laser cavities on silicon-on-insulator for monolithic integrated light sources. Applied Physics Letters, 2016, 108, .	3.3	14
15	Axial InAs(Sb) inserts in selective-area InAsP nanowires on InP for optoelectronics beyond 25 Âµm. Optical Materials Express, 2018, 8, 1075.	3.0	12
16	Enhanced Carrier Multiplication in InAs Quantum Dots for Bulk Avalanche Photodetector Applications. Advanced Optical Materials, 2017, 5, 1601023.	7.3	10
17	Selective-area InAsSb Nanowires on InP for 3 â€“ 5 Î¼m Mid-wavelength Infrared Optoelectronics. MRS Advances, 2017, 2, 3565-3570.	0.9	7
18	Exploring time-resolved photoluminescence for nanowires using a three-dimensional computational transient model. Nanoscale, 2018, 10, 7792-7802.	5.6	7

#	Article	IF	Citations
19	Performance of IEEE 802.11 MAC in Underwater Wireless Channels. Procedia Computer Science, 2012, 10, 62-69.	2.0	5
20	Reflection spectromicroscopy for the design of nanopillar optical antenna detectors. , 2014, , .		2
21	Feasibility of room-temperature mid-wavelength infrared photodetectors using InAsSb nanostructured photoabsorbers. , 2018, , .		2